

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Fumiyoshi ONO

Appln. No.: 09/672,776

Confirmation No.: not yet assigned

Group Art Unit: 1765

Filed: September 29, 2000

Examiner: C. Brown

For: COMPOSITION FOR POLISHING METAL ON SEMICONDUCTOR WATER AND
METHOD OF USING SAME

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

This Amendment is submitted in response to the Office Action dated December 6, 2000, in which the Examiner set a three-month period for response.

Please amend the above-identified application as follows:

IN THE CLAIMS:

Please enter the following amended claims:

6. (Amended) A method for polishing a metal film on a semiconductor substrate, comprising the steps of:

providing a semiconductor substrate comprising a metal film and an insulating film therein;

providing a polishing composition comprising alumina fine particles containing or not containing aluminum hydrate, a polishing accelerator and water, said alumina fine particles having an α conversion ratio of from 65 to 90% and a specific surface



#43
38101
MW
RECEIVED
MAR -7 2001
TC 170 MAIL ROOM

BEST AVAILABLE COPY